

Silicon NPN Power Transistors

2N3226

DESCRIPTION

- With TO-3 package
- Excellent safe operating area
- Low collector saturation voltage

APPLICATIONS

- For power amplifier and switching circuits applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

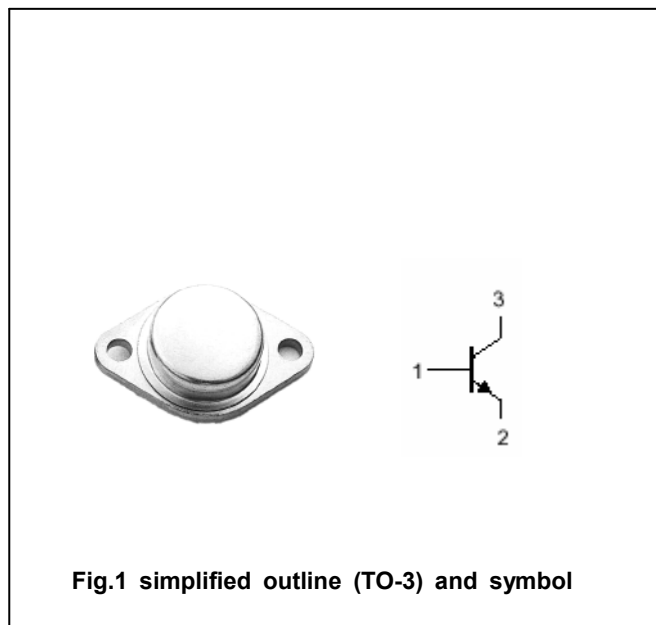


Fig.1 simplified outline (TO-3) and symbol

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	35	V
V_{CEO}	Collector-emitter voltage	Open base	35	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		5	A
P_D	Total power dissipation	$T_C=25^\circ\text{C}$	75	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-65~200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{(th)jc}$	Thermal resistance junction to case	1.17	$^\circ\text{C}/\text{W}$

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CHARACTERISTICS

 $T_j=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	$I_C=0.2A ; I_B=0$	35			V
$V_{CE(sat)-1}$	Collector-emitter saturation voltage	$I_C=3A ; I_B=0.3A$			1.0	V
$V_{CE(sat)-2}$	Collector-emitter saturation voltage	$I_C=5A ; I_B=1.0A$			2.0	V
$V_{BE(on)}$	Base-emitter on voltage	$I_C=3A ; V_{CE}=4V$			2.0	V
I_{CEO}	Collector cut-off current	$V_{CE}=35V ; I_B=0$			1.0	mA
I_{CBO}	Collector cut-off current	$V_{CB}=35V ; I_E=0$			0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V ; I_C=0$			0.1	mA
h_{FE-1}	DC current gain	$I_C=1A ; V_{CE}=4V$	40			
h_{FE-2}	DC current gain	$I_C=3A ; V_{CE}=4V$	20			

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PACKAGE OUTLINE

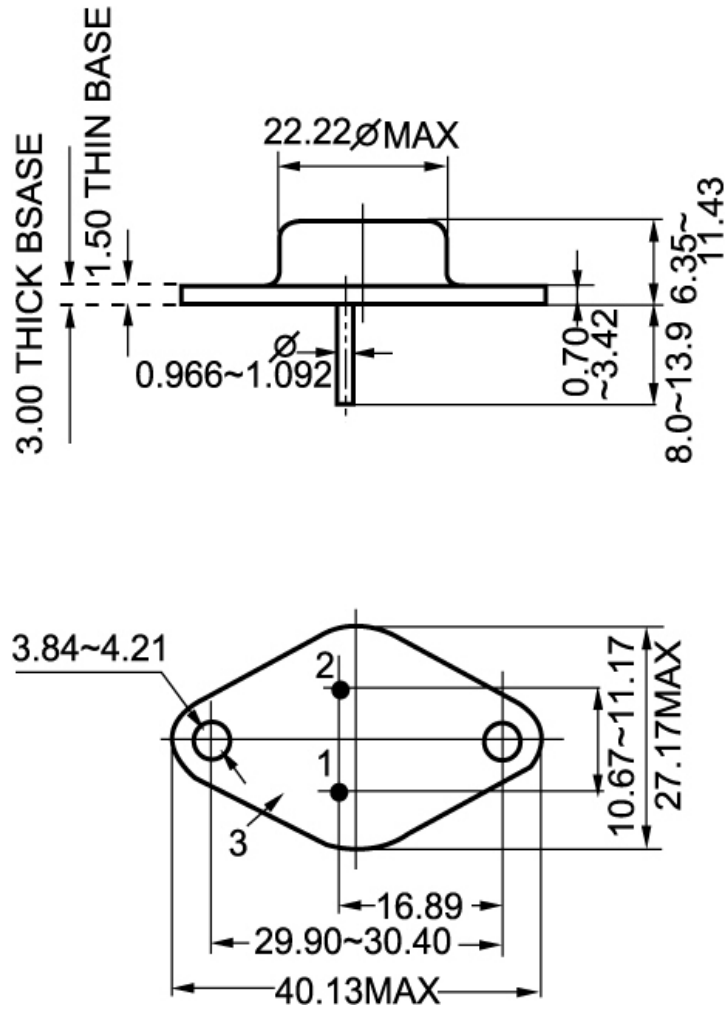


Fig.2 outline dimensions (unindicated tolerance: $\pm 0.1\text{mm}$)